



DRV8308 SLVSCF7-FEBRUARY 2014

DRV8308 Brushless DC Motor Controller

Technical

Documents

Sample &

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1 Features

- Three-phase Brushless DC Motor Controller
 - Fully Digital Speed Loop With Programmable Gain and Loop Filters
 - Clock Input or PWM Inputs for Speed Control
- Operating Supply Voltage 8.5 to 32 V
- Drives 10- to 130-mA Gate-Drive Current to 6 N-Channel MOSFETs With Adjustable Slew Rates
- Supports Sensor-based Sinusoidal and Trapezoidal Commutation Control With Tunable Delay
- Flexible Configuration Methods:
 - Serial Control
 - Internal OTP Memory
 - External EEPROM
- 5-V Linear Regulator and Switched Power Output for Hall Sensors
- SPI Control Interface
- Low-power Standby Mode
- Locked Rotor Detection and Restart
- Integrated Overcurrent, Overvoltage, and . Overtemperature Protection
- 6 × 6-mm QFN Package, 0.5-mm Pitch

Applications 2

- **Pumps and Industrial Equipment**
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3 Description

Tools &

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The DRV8308 device is a three half-bridge pre-driver that drives up to 130 mA to six N-type MOSFETs with a single power supply. Aimed at sensored threephase brushless DC motors, this pre-driver includes configurable a digital speed loop, speed controls, and commutation modes to optimize motor performance. When properly tuned, the DRV8308 device can drive motors with less than 0.1% cycle jitter and fast torque compensation.

Support &

Community

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The integrated digital speed loop allows the motor to maintain speed under variable loads with programmable gain and loop filters. The adjustable slew rates can also lower the switching noise and improve EMC.

The DRV8308 device also supports both the 120° and 180° commutation modes with the ability to adjust the delay to increase power efficiency. For high-performance systems, sinusoidal (180°) commutation mode is used to minimize acoustic noise and torque ripple. Jitter caused by non-ideal Hall placement and matching can be eliminated once constant speed is reached by switching from three Hall sensor phases to just a single Hall sensor.

In addition to advanced programmability features to tune the motor's performance, the SPI interface also provides detailed fault reporting such as locked rotor detection. overcurrent. overtemperature, and overvoltage, as well as charge pump short and failure, to provide robust protection and intelligence to the overall system design.

Device Information				
ORDER NUMBER	PACKAGE (PIN)	BODY SIZE		
DRV8308RHAR	RHA (40)	6-mm × 6-mm		
DRV8308RHAT	RHA (40)	6-mm × 6-mm		

Simplified Schematic

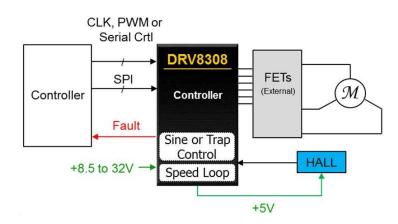






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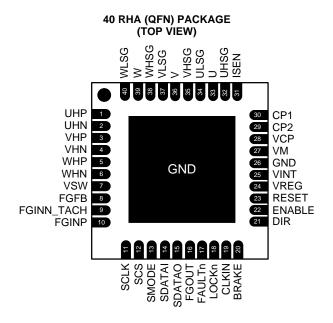
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5 Revision History

Date	Revision	Notes
February 2014	*	Initial Release



6 Terminal Configurations and Functions



Terminal Functions

TERMI	NAL	I/O ⁽¹⁾	DECODIDION				
		1000	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS			
POWER AND G	ROUND						
CP1	30	I/O	Charge pump flying capacitor	Connect a 0.1-µF 35-V capacitor between CP1 and CP2			
CP2	29	I/O		Connect a 0.1-pr 35-V capacitor between CFT and CF2			
GND	26, PPAD	I	Ground reference. Pin 26 and the Power Pad are internally connected.	Connect to board GND			
VCP	28	I/O	Charge pump storage capacitor	Connect a 1-µF 35-V ceramic capacitor to VM			
VINT	25	I/O	Internal 1.8-V core voltage regulator bypass	Bypass to GND with a $1-\mu F$ 6.3-V ceramic capacitor			
VM	27	I	I Motor supply voltage Connect to motor supply voltage. Bypass to GND with a 0.1-μF ceramic capacitor, plu electrolytic capacitor (47 μF or larger is recommende a voltage rating of 1.5× to 2.5× VM.				
VREG	24	I/O	5-V regulator output. Active when ENABLE is active.	Bypass to GND with a 0.1- μ F 10-V ceramic capacitor. Can provide 5-V power to Hall sensors.			
VSW	7	0	Switched VM power output. When ENABLE is active, VM is applied to this pin.	Can be used for powering Hall elements, along with added series resistance.			
CONTROL							
BRAKE	20	I	Causes motor to brake. Polarity is programmable. Internal pulldown resistor.				
CLKIN	19	Ι	The clock input, used in Clock Frequency mode and Clock PWM mode. Internal pulldown resistor.				
DIR 21 I Sets motor rotation direction. Polarity is programmable. Internal pulldown resistor.							
ENABLE	22	I	Enables and disables motor. Polarity is programmable. Internal pulldown resistor.				

(1) I = input, O = output, OD = open-drain output, I/O = input/output

Terminal Functions (continued)

TERMIN	IAL	110 (1)					
NAME	NUMBER	I/O ⁽¹⁾	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS			
FAULTn	17	OD	Fault indicator – active low when overcurrent, overtemperature, or rotor stall detected. Open-drain output.				
FGOUT	16	OD	Outputs a TACH signal generated from the FG amplifier or Hall sensors. Open-drain output.				
LOCKn	18	OD	Outputs a signal that indicates the speed loop is locked. Open-drain output.				
RESET	23	I	Active high to reset all internal logic. Internal pulldown resistor.				
SERIAL INTERI	FACE			·			
SCLK ⁽²⁾	11	I/OD	Serial clock	SPI mode: Serial clock input. Data is clocked on rising edges. Internal pulldown resistor. EEPROM mode: Connect to EEPROM CLK. Open-drain output requires external pullup.			
SCS ⁽²⁾	12	I/OD	Serial chip select	SPI mode: Active high enables serial interface operation. Internal pulldown resistor. EEPROM mode: Connect to EEPROM CS. Open-drain output requires external pullup.			
SDATAI	14	I	Serial data input	SPI mode: Serial data input. Internal pulldown resistor. EEPROM mode: Serial data input. Connect to EEPROM DO pin.			
SDATAO	15	OD	Serial data output	SPI mode: Serial data output. Open-drain output. EEPROM mode: Connect to EEPROM DI. Open-drain output requires external pullup.			
SMODE	13	I	Serial mode	SPI mode: leave open or connect to ground for SPI interface mode. EEPROM mode: Connect to logic high to for EEPROM mode.			
POWER STAGE	E INTERFAC	E					
ISEN	31	Ι	Low-side current sense resistor	Connect to low-side current sense resistor			
U	33	Ι					
V	36	I	Measures motor phase voltages for V _{FETOCP}	Connect to motor windings			
W	39	Ι	FEIOCP				
UHSG	32	0					
VHSG	35	0	High-side FET gate outputs	Connect to high-side 1/2-H N-channel FET gate			
WHSG	38	0					
ULSG	34	0					
VLSG	37	0	Low-side FET gate outputs	Connect to low-side 1/2-H N-channel FET gate			
WLSG	40	0					
HALL AND FG	INTERFACE			·			
FGFB	8	0	FG amplifier feedback pin	Connect feedback network to FGIN-			
FGINN_TACH	9	I ⁽³⁾	FG amplifier negative input or TACH input	Connect to FG trace and filter components. When using a TACH with FGSEL= 3, connect a logic-level TACH signal. If unused, connect FGFB to FG–.			
FGINP	10	I/O	FG amplifier positive input	Connect to FG trace and filter components on the PCB (if used).			

(2) In SPI mode, these pins are inputs; in EEPROM mode, they are open-drain outputs.
(3) When using FG amp, this pin is an analog input. If in TACH mode, this is a logic-level input.



Terminal Functions (continued)

TERMI	NAL	I/O ⁽¹⁾	DESCRIPTION		
NAME	NUMBER	100	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS Connect to Hall sensors. Noise filter capacitors may be desirable, connected between the + and – Hall inputs.	
UHP	1	I	Hall sensor U positive input		
UHN	2	I	Hall sensor U negative input		
VHP	3	I	Hall sensor V positive input		
VHN	4	Т	Hall sensor V negative input	desirable, connected between the + and - Hall inputs.	
WHP	5	Ι	Hall sensor W positive input		
WHN	6	Ι	Hall sensor W negative input		

Specifications 7

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)(2)(3)

	MIN	MAX	UNIT
Power supply voltage range (VM)	-0.3	35	V
Charge pump and high side gate drivers (VCP, UHSG, VHSG, WHSG)	-0.3	50	V
Output pin, low side gate drivers, charge pump flying cap and switched VM power supply voltage range (U, V, W, ULSG, VLSG, WLSG, CP1, CP2 VSW)	-0.6	40	V
Internal core voltage regulator (VINT)	-0.3	2.0	V
Linear voltage regulator output (VREG)	-0.3	5.5	V
Sense current pin (ISEN)	-0.3	2.0	V
Digital pin voltage range (SCLK, SCS, SMODE, SDATAI, SDATAO, FGOUT, FAULTn, LOCKn, CLKIN, BRAKE, DIR, ENABLE, RESET)	-0.5	5.75	V
Hall sensor input pin voltage (UHP, UHN, VHP, VHN, WHP, WHN, FGFB, FGINN/TACH, FGINP)	0	VREG	V
Continuous total power dissipation	See Thermal Info	rmation	
Operating junction temperature range, T _J	-40	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) (3) All voltage values are with respect to network ground terminal.

Power dissipation and thermal limits must be observed

7.2 Handling Ratings

over operating free-air temperature range (unless otherwise noted)

PARAMETER	DEFINITION	MIN	MAX	UNIT
T _{STG}	Storage temperature range	-60	150	°C

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM MAX	UNIT
VM	Motor power supply vo	Itage range, ENABLE = 1, motor operating ⁽¹⁾	8.5	32	V
V _{MDIS}	Motor power supply vo	Itage range, ENABLE = 0, motor not operating	4.5	35	v
I _{VREG}	VREG output current ⁽²)	0	30	~ ^
I _{VSW}	VSW output current ⁽²⁾		0	30	mA
f _{HALL}	Hall sensor input frequ	ency ⁽³⁾	0	30	
4		SPDMODE = 00 (Clock frequency mode)	0	90	kHz
† _{CLKIN}	Frequency on CLKIN	SPDMODE = 01 (Clock PWM mode)	16	50 ⁽⁴⁾	

Note that at VM < 12 V, gate drive output voltage tracks VM voltage Power dissipation and thermal limits must be observed (1)

(2)

(3) (4)

 f_{HALL} of 50 Hz to 6.7 kHz is best Operational with frequencies above 50 kHz, but resolution is degraded



7.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DRV8308	
		RHA (40 PINS)	UNIT
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	32.0	
θ _{JCtop}	Junction-to-case (top) thermal resistance ⁽³⁾	24.5	
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	9.9	°C 11/
Ψ_{JT}	Junction-to-top characterization parameter ⁽⁵⁾	2.7	°C/W
Ψ_{JB}	Junction-to-board characterization parameter ⁽⁶⁾	10.0	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	2.7	

For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
 The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as

specified in JESD51-7, in an environment described in JESD51-2a.
(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC standard

test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter, ψ_{JB} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

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7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VM SUPF	PLY					
I _{VM}	VM active current	ENABLE = active, VREG and VSW open		12	18	mA
I _{STBY}	VM standby current	ENABLE = inactive			120	μA
V	VM logic reset voltage	VM falling			4.6	V
V _{RESET}	vivi logic teset voltage	VM rising	5.0			v
VREG SL	JPPLY					
V _{VREG}	Output voltage	$I_{OUT} = 1$ to 30 mA	4.75	5	5.25	V
I _{VREG}	Output current				30	mA
VSW SU	PPLY					
R _{DS(ON)}	VSW switch on-resistance	$I_{OUT} = 1$ to 30 mA		9	20	Ω
I _{VSW}	Output current				30	mA
INTERNA	L CLOCK OSCILLATOR					
f _{CLK50}	Internal CLK50 clock frequency			50		MHz
LOGIC-L	EVEL INPUTS AND OUTPUTS					
V _{IL}	Low-level input voltage				0.8	V
VIH	High-level input voltage		1.5		5.5	V
I _{IL}	Low-level input current		-50		50	μA
		V _{IN} = 3.3 V, RESET,				μA
	Lligh lovel input surrent	DIR, BRAKE, CLKIN, SCS, SCLK, SDATAI,	20		100	
IIH	High-level input current	SMODE				
		V _{IN} = 3.3 V, ENABLE	6		9	
V _{HYS}	Input hysteresis voltage		0.1	0.3	0.5	V
		RESET, DIR, BRAKE,				kΩ
R _{PD}	Input pulldown resistance	CLKIN, SCS, SCLK, SDATAI, SMODE	50	100	150	
FD		ENABLE	350		550	
	RAIN OUTPUTS		000		550	
V _{OL}	Low-level output voltage	I _{OUT} = 2.0 mA			0.5	V
I _{OH}	Output leakage current	$V_{OUT} = 3.3 V$			0.0	μA
-		V001 - 0.0 V				μΛ
V _{IO}	FG amplifier input offset voltage		-7		7	mV
I _{IB}	FG amplifier input bias current				1	μΑ
V _{ICM}	FG amplifier input common mode voltage range		1.5		3.5	μ <u>μ</u> V
A _V	FG amplifier open loop voltage gain		45		0.0	dB
GBW	FG amplifier gain bandwidth product		500			kHz
V _{REF+}	FG comparator positive reference voltage		-20%	V _{VREG} / 2	20%	V
V _{IT+}	FG comparator positive threshold		-20%	V _{VREG} / 2 V _{VREG} / 1.8	20%	V
VIT+ VIT-	FG comparator negative threshold		-20%	V _{VREG} / 1.0 V _{VREG} / 2	20%	V
	NSOR INPUTS		2070	VREG / 2	2070	v
V _{HYS}	Hall amplifier hysteresis voltage		15	20	25	mV
⊻hys ∆V _{HYS}	Hall amplifier hysteresis voltage	Between U, V, W	-5	20	25 5	mV
	Hall amplifier input differential				5	mV
V _{ID}	Hall amplifier input common mode voltage					V
V _{CM}	range		1.5		3.5	v
I _{IN}	Input leakage current	H_x+ = H_x-	-10		10	μA
t _{HDEG}	Hall deglitch time			20		μs
	DRIVERS	I				۳۵

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
V _{OUTH}	High-side gate drive output voltage	$I_0 = 100 \ \mu A, \ VM \ge 12V$		VM + 10		V		
V _{OUTL}	Low-side gate drive output voltage	I _O = 100 μA		10		V		
		IDRIVE = 000		10				
		IDRIVE = 001		20				
		IDRIVE = 010		30				
		IDRIVE = 011		50				
I _{OUT}	Peak gate drive current	IDRIVE = 100		90		mA		
		IDRIVE = 101		100				
		IDRIVE = 110		110				
		IDRIVE = 111		130				
CYCLE-BY	-CYCLE CURRENT LIMITER							
V _{LIMITER}	Voltage limit across R _{ISENSE} for the current limiter		0.225	0.25	0.275	V		
		OCPDEG = 00		2.0				
	Time that V_{LIMITER} is ignored, from the start of	OCPDEG = 01		3.0				
t _{BLANK}	the PWM cycle	OCPDEG = 10		3.75		μs		
		OCPDEG = 11		6				
PROTECTI	ON CIRCUITS							
V _{SENSEOCP}	Voltage limit across R _{ISENSE} for overcurrent protection		1.7	1.8	1.9	V		
		OCPDEG = 00		1.6				
		OCPDEG = 01		2.3				
t _{SENSEOCP}	Deglitch time for V _{SENSEOCP} to trigger	OCPDEG = 10		3		μs		
		OCPDEG = 11		5				
		OCPTH = 00	200	250	400			
	Voltage limit across each external FET's drain	OCPTH = 01	400	500	600			
V _{FETOCP}	to source for overcurrent protection	OCPTH = 10	600	750	850	mV		
		OCPTH = 11	850	1000	1200			
		OCPDEG = 00		1.6				
		OCPDEG = 01		2.26				
t FETOCP	Deglitch time for V _{FETOCP} to trigger	OCPDEG = 10		3		μs		
		OCPDEG = 11		5				
		VM rising		8				
V _{UVLO}	VM undervoltage lockout	VM falling		7.8		V		
		VM rising, OVTH = 0	32	34	36			
V _{OVLO}	VM overvoltage lockout	VM rising, OVTH = 1	02	τŪ	29	V		
toctov	Fault retry time after RLOCK or OTS	RETRY = 1		5	20	S		
t _{RETRY}	Thermal shutdown die temperature		150	160		°C		
T _{TSD}	memai shutuown die temperature	LRTIME = 00	130	100		U		
t _{LOCK}	Locked rotor detect time	LRTIME = 01		3		s		
		LRTIME = 10		5				
. ,		LRTIME = 11		10				
V _{CPFAIL}	VCP failure threshold (CPFAIL bit)			VM + 3.0		V		

7.6 SPI Timing Requirements

NUMBER ⁽¹⁾	PARAMETER	TEST CONDITIONS ⁽²⁾	MIN	MAX	UNIT
1	t _{CYC}	Clock cycle time	62		
2	t _{CLKH}	Clock high time	25		
3	t _{CLKL}	Clock low time	25		
4	t _{SU(SDATI)}	Setup time, SDATI to SCLK	5		
5	t _{H(SDATI)}	Hold time, SDATI to SCLK	1		ns
6	t _{SU(SCS)}	Setup time, SCS to SCLK	5		
7	t _{H(SCS)}	Hold time, SCS to SCLK	1		
8	t _{L(SCS)}	Inactive time, SCS (between writes)	100		
9	t _{D(SDATO)}	Delay time, SCLK to SDATO (during read)		10	
	t _{AWAKE}	Wake time (ENABLE active to high-side gate drive enabled)		1	ms
	t _{SPI}	Delay from power-up or RESET low until serial interface functional		10	μs

 $T_A = 25^{\circ}C$, over recommended operating conditions unless otherwise noted

(1) These numbers refer to the corresponding number in Figure 1

(2) SMODE = Low

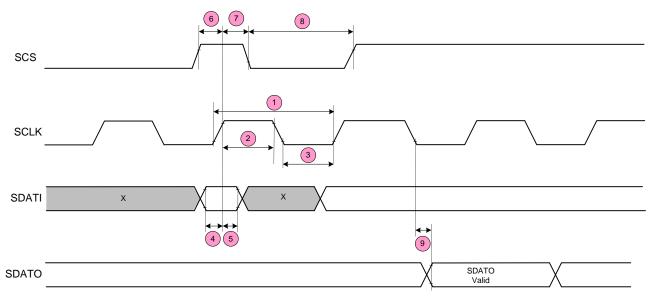


Figure 1. SPI Timing Requirements



8 Detailed Description

8.1 Overview

The DRV8308 device controls 3-phase brushless DC motors using a speed and direction input interface and Hall signals from the motor. The device drives N-channel MOSFETs with 10-V V_{GS} , and a configurable gate drive current of 10 to 130 mA.

There are three modes of speed input: clock frequency, clock duty cycle (pulse-width modulation), and an internal register that specifies duty cycle. In the clock frequency mode, the device's digital speed control system matches motor speed with the input clock's frequency. Motor speed is either determined from the Halls sensors or signal on the FG input, which can be generated from a board trace underneath the motor that senses magnetic reluctance. The speed control system offers digital tuning of pole and zero frequencies and integrator gain. When properly tuned, the DRV8308 can drive motors with < 0.1% cycle jitter and fast torque compensation for varying loads. The duty cycle speed modes operate in open-loop without speed control.

When the DRV8308 device powers up, the configuration registers are set from either the one-time programmable (OTP) non-volatile memory, or from an external EEPROM (depending on the SMODE pin). After power-up, registers can be set in realtime over SPI, and the OTP memory can be permanently written once.

When the DRV8308 device begins spinning a motor, it initially uses all three Hall sensor phases to commutate. After a constant speed is reached, the LOCKn pin is pulled low and only one Hall sensor becomes used; this feature reduces jitter by eliminating the error caused by non-ideal Hall device placement and matching. Also at this time, commutation transitions to sine wave current drive (if enabled), which minimizes acoustic noise and torque ripple. Commutation timing can be tuned using the ADVANCE register for optimal performance and power efficiency.

Numerous protection circuits prevent system components from being damaged during adverse conditions. Monitored aspects include motor voltage and current, gate drive voltage and current, device temperature, and rotor lockup. When a fault occurs, the DRV8308 device stops driving and pulls FAULTn low, in order to prevent FET damage and motor overheating.

The DRV8308 device is packaged in a compact 6×6 -mm, 40-pin QFN with a 0.5-mm pin pitch, and operates through an industrial ambient temperature range of -40° C to 85° C.



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8.2 Functional Block Diagram

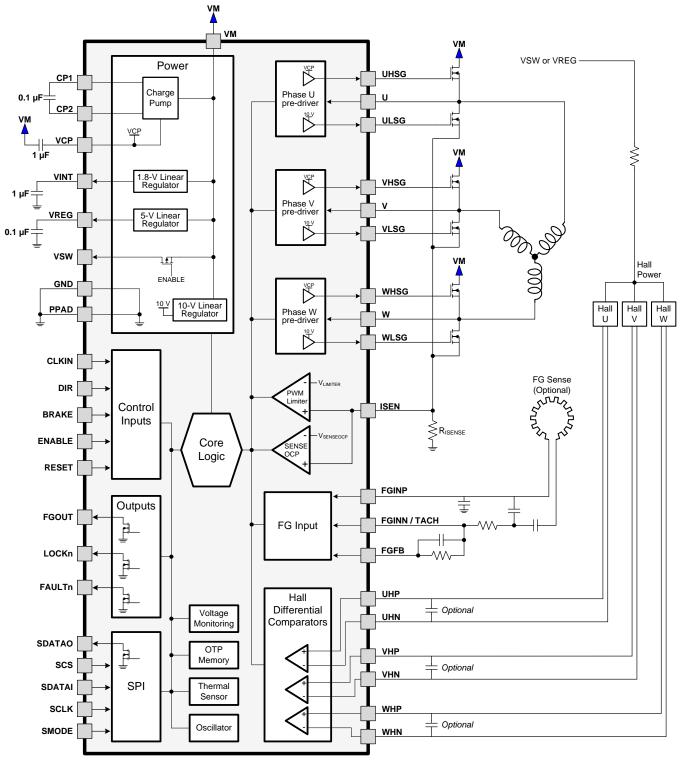


Figure 2.



8.3 Feature Description

8.3.1 Hall Comparators

Three comparators are provided to process the raw signals from Hall effect transducers to commutate the motor. The Hall amplifiers sense zero crossings of the differential inputs and pass the information to digital logic.

The Hall amplifiers have hysteresis, and their detect threshold is centered at 0. Note, hysteresis is defined as shown in Figure 3:

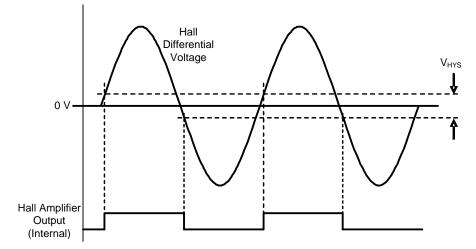


Figure 3. Hall Amplifier Hysteresis

In addition to the hysteresis, the Hall inputs are deglitched with a circuit that ignores any extra Hall transitions for a period of 20 μ s after sensing a valid transition. This prevents PWM noise from being coupled into the Hall inputs, which can result in erroneous commutation.

If excessive noise is still coupled into the Hall comparator inputs, it may be necessary to add capacitors between the + and – inputs of the Hall comparators, and (or) between the input or inputs and ground.

The ESD protection circuitry on the Hall inputs implements a diode to VREG. Because of this diode, the voltage on the Hall inputs should not exceed the VREG voltage.

Since VREG is disabled in standby mode (ENABLE inactive), the Hall inputs should not be driven by external voltages in standby mode. If the Hall sensors are powered from VREG or from VSW, this is specified by the DRV8308 device; however, if the Hall sensors are powered externally, they should be disabled if the DRV8308 is put into standby mode. In addition, they should be powered-up before enabling the motor, or an invalid Hall state may cause a delay in motor operation.

8.3.2 FG Amplifier, Comparator, and FG Output

An FG amplifier and comparator provide rotational feedback from an external magnetic reluctance sensor. A diagram of the FG circuit is shown in Figure 4:

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Feature Description (continued)

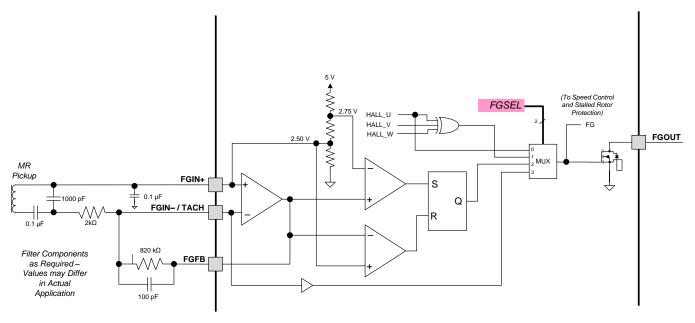


Figure 4. FG Circuit Diagram

The output of the FG amplifier is provided on a pin, so the gain of the FG amplifier can be set by the user. Filter circuits can also be implemented.

Note that the FG signal is also fed back internally to the speed control circuits.

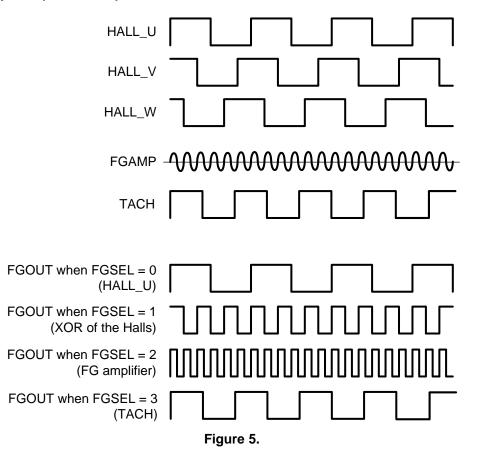
The FG signal that the DRV8308 device uses can be generated from a PCB trace under a motor, or it can be input from a logic-level TACH input, or it can be synthesized from the Hall sensor transitions (selectable by register FGSEL). If generated from Hall transitions, the resulting output can be either an exclusive-or function of the three Hall sensors, or the same as the HALL_U input, as shown in Figure 5.

Selection of FG operating mode is through the FGSEL register bits.

The FGOUT pin is an open-drain output and requires an external pullup resistor to the logic supply.



Feature Description (continued)



8.3.3 Enable, Reset, and Clock Generation

The ENABLE pin is used to start and stop motor operation. ENABLE can be programmed to be active high or active low, depending on the state of the ENPOL bit; if ENPOL = 0, ENABLE is active high. If ENPOL = 1, the ENABLE pin is active low.

The polarity of ENABLE cannot be modified during operation through register writes; it is controlled only by the contents of the ENPOL bit in OTP memory.

When ENABLE is active, operation of the motor is enabled. When ENABLE is made inactive, the speed control loop is reset, and the motor either brakes or coasts depending on the state of the BRKMOD bit. After motor rotation has stopped (when no transitions occur on the FGOUT pin for a period of 1 s), the DRV8308 device enters a low-power standby state. In the standby state, the motor driver circuitry is disabled (all gate drive outputs are driven low, so the FET outputs are high-impedance), the gate drive regulator and charge pump are disabled, the VREG regulator and VSW power switch are disabled, and all analog circuitry is placed into a low power state. The digital circuitry in the device still operates in standby mode.

All internal logic is reset in three different ways:

- 1. Upon device power-up.
- 2. When VM drops below V_{RESET} .
- 3. When the RESET pin is high while ENABLE is active.

If RESET is high while ENABLE is inactive, then the registers read as 1. If the RESET pin is not needed, it can be connected to GND. The RESET input is deglitched with a 10-µs timer on assertion and deassertion.

An internal clock generator provides all timing for the DRV8308 device. The master oscillator runs at 100 MHz. This clock is divided to a nominal 50-MHz frequency that clocks the remainder of the digital logic.

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Feature Description (continued)

8.3.4 Commutation

For 3-phase brushless DC motors, rotor position feedback is provided from Hall effect transducers mounted on the motor. These transducers provide three overlapping signals, each 60° apart. The windings are energized in accordance with the signals from the Hall sensors to cause the motor to move.

In addition to the Hall sensor inputs, commutation is affected by a direction control, which alters the direction of motion by reversing the commutation sequence. Control of commutation direction is by the DIRPOL register bit as well as the DIR input pin. The DIRPOL register bit is combined with the pin with an exclusive-OR function as follows:

DIR Pin	DIRPOL Register Bit	Resulting DIR for Commutation
0	0	0
0	1	1
1	0	1
1	1	0

 Table 1. Direction Behavior

If the commanded direction is changed while the motor is moving, the device either brakes or allows the motor to coast, depending on the state of the BRKMODE bit, until the motor stops. The stopped condition is determined by measuring the period of the HALL_U signal; when the period exceeds 160 ms, typical operation resumes and the motor starts spinning in the commanded direction. This prevents excessive current flow in the output stage if the motor is reversed while running at speed.

The DRV8308 device supports three commutation modes: standard 120° commutation using three Hall sensors, 120° commutation using a single Hall sensor, and 180° sine-wave-drive commutation.

In standard 120° commutation, mis-positioning of the Hall sensors can cause motor noise, vibration, and torque ripple. 120° commutation using a single Hall sensor (single-Hall commutation) can improve motor torque ripple and vibration because it relies on only one Hall edge for timing.

180° sine-wave-drive commutation is even more advanced, and excites the windings with a waveform that delivers nearly sinusoidal current to each winding.

8.3.4.1 120° 3-Hall Commutation

In standard 120° commutation, the motor phases are energized using simple combination logic based on all three Hall sensor inputs.

Standard 120° commutation is in accordance with Table 2, Figure 6, and Figure 7:

		I	HALL I	NPUTS	5				PRE-DRIV	E OUTPUTS		
STATE	I	DIR = 1 DIR = 0			Pha	se U	Phase V Phase W			se W		
	U_H	V_H	W_H	U_H	V_H	W_H	U_HSGATE	U_HSGATE U_LSGATE		V_LSGATE	W_HSGATE	W_LSGATE
1	L	L	Н	н	Н	L	L	L	PWM	L / !PWM ⁽²⁾	L	Н
2	L	Н	Н	Н	L	L	PWM	L / !PWM ⁽²⁾	L	L	L	Н
3	L	Н	L	н	L	Н	PWM	L / !PWM ⁽²⁾	L	Н	L	L
4	Н	Н	L	L	L	Н	L	L	L	Н	PWM	L / !PWM ⁽²⁾
5	Н	L	L	L	Н	Н	L	Н	L	L	PWM	L / !PWM ⁽²⁾
6	Н	L	Н	L	Н	L	L	Н	PWM	L / !PWM ⁽²⁾	L	L
1X	Н	Н	Н	L	L	L	L	L	L	L	L	L
2X	L	L	L	н	Н	Н	L	L	L	L	L	L

Table 2. Standard 120° Commutation⁽¹⁾

(1) Hall sensor is "H" if the positive input pin voltage is higher than the negative input pin voltage. States 1X and 2X are illegal input combinations.

(2) During states where the phase is driven with a PWM signal, using asynchronous rectification, the LS gate is held off (L); using synchronous rectification, the LS gate is driven with the inverse of the HS gate.

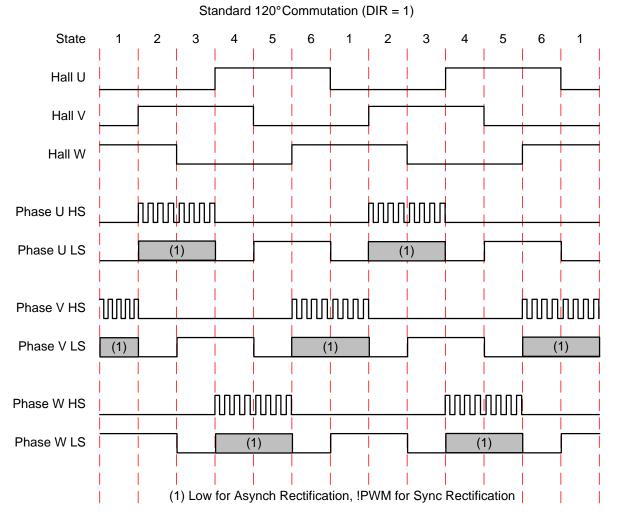


Figure 6. Standard 120° Commutation (DIR = 1)



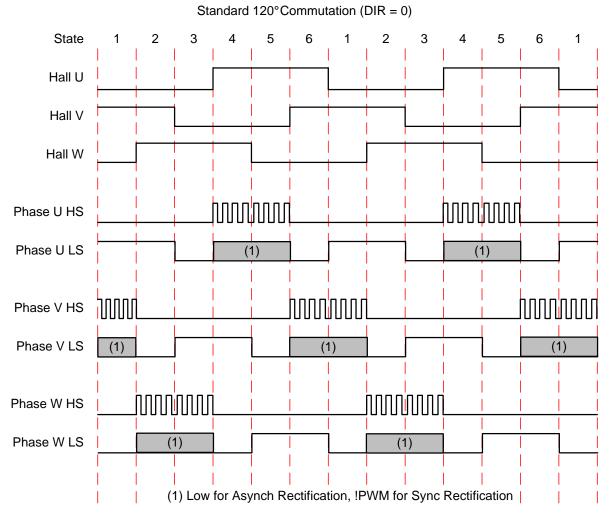


Figure 7. Standard 120° Commutation (DIR = 0)

8.3.4.2 120° Single-Hall Commutation

To generate commutation timing for single-Hall commutation, a digital timer is used to create a clock that runs at 960× the Hall sensor frequency. Only one Hall sensor input, HALL_U, is used for commutation; this eliminates any torque ripple caused by mechanical or electrical offsets of individual Hall sensors.

Single-Hall commutation is only enabled when the register BASIC = 0 and the motor is operating at a nearly constant speed or speed-locked condition. To control this function, logic is used to determine when the speed is constant and the speed control loop is locked. This logic generates the LOCK signal. The LOCK signal is also output on the LOCKn pin.

Except in PWM input modes, LOCK is also prevented from being signaled if the speed control loop integrator is saturated (either at 0 or full-scale), which indicates that the speed control loop is not locked.

Until LOCK goes active (for example, at start-up, stop, or application of a sudden load that causes motor speed to drop very quickly), standard 120° commutation is used. Because of this, three Hall sensors are required regardless of which commutation method is used.

The commutation timer drives a counter that can be offset with a value programmed in the ADVANCE register. This value allows the phase of commutation to be shifted relative to the actual Hall sensor transitions. Note that the phase advance is not functional in standard 120° commutation. The phase advance also has an automatic mode where the advance value is scaled according to motor speed (see Auto Gain and Advance Compensation).



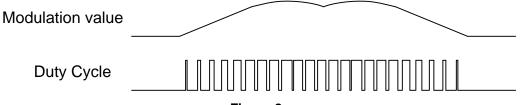
Timing of 120° single-Hall commutation is essentially the same as standard 120° commutation shown previously. However, there are small time differences of when the transitions occur.

8.3.4.3 180° Sine-Wave-Drive Commutation

180° sine-wave-drive commutation uses a single Hall sensor to generate commutation timing, as described for 120° single-Hall commutation. In addition, the value of the commutation timer modulates the duty cycle of the outputs in accordance with a fixed pattern that approximates sinusoidal current through the windings.

The output of the commutation block is a 12-bit modulation value for each motor phase (U, V, and W) that represents the duty cycle modulation of the PWM for each output. Note that during 120° commutation, these values are either 0 or set to a constant value derived from the MOD120 register.

To make a smooth transition from 120° operation to 180° operation the MOD120 register should be set to a value of 3970.





During 180° sine-wave-drive commutation, commutation transitions occur midway between Hall transitions. The PWM duty cycle is modulated to provide sinusoidal current waveforms. Commutation (shown for asynchronous rectification) is in accordance with the table and diagrams below. Note that the diagrams show a representation of duty cycle, not level, for the PWM states.

			HALL I	NPUTS	5		PRE-DRIVE OUTPUTS						
STATE	DIR = 1			-	DIR = 0)	Pha	se U	Phase V		Phase W		
	U_H	V_H	W_H	U_H	V_H	W_H	U_HSGATE	U_LSGATE	V_HSGATE	V_LSGATE	W_HSGATE	W_LSGATE	
1	L	L	Н	Н	Н	L	PWM	L / !PWM ⁽²⁾	PWM	L / !PWM ⁽²⁾	L	Н	
2	L	Н	Н	Н	L	L	PWM	L / !PWM ⁽²⁾	PWM	L / !PWM ⁽²⁾	L	Н	
3	L	н	L	Н	L	Н	PWM	L / !PWM ⁽²⁾	L	Н	PWM	L / !PWM ⁽²⁾	
4	Н	Н	L	L	L	Н	PWM	L / !PWM ⁽²⁾	L	Н	PWM	L / !PWM ⁽²⁾	
5	Н	L	L	L	Н	Н	L	Н	PWM	L / !PWM ⁽²⁾	PWM	L / !PWM ⁽²⁾	
6	Н	L	Н	L	Н	L	L	Н	PWM	L / !PWM ⁽²⁾	PWM	L / !PWM ⁽²⁾	
1X	Н	н	Н	L	L	L	L	L	L	L	L	L	
2X	L	L	L	Н	Н	Н	L	L	L	L	L	L	

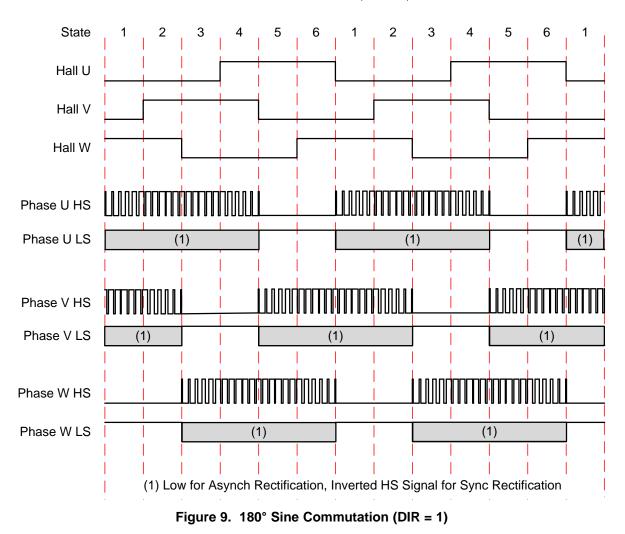
Table 3. Commutation for Asynchronous Rectification⁽¹⁾

(1) Hall sensor is "H" if the positive input pin voltage is higher than the negative input pin voltage. States 1X and 2X are illegal input combinations.

(2) During states where the phase is driven with a PWM signal, using asynchronous rectification, the LS gate is held off (L); using synchronous rectification, the LS gate is driven with the inverse of the HS gate.



180° Sine Commutation (DIR = 1)





180° Sine Commutation (DIR = 0) 2 2 State 6 5 4 3 1 6 5 4 3 1 6 Hall U Hall V Hall W Phase U HS Phase U LS (1) (1) Phase V HS Phase V LS (1) (1) (1) Phase W HS Phase W LS (1) (1) (1) (1) Low for Asynch Rectification, Inverted HS Signal for Sync Rectification

Figure 10. 180° Sine Commutation (DIR = 0)

8.3.5 Commutation Logic Block Diagram

A block diagram of the commutation logic is shown in Figure 11.

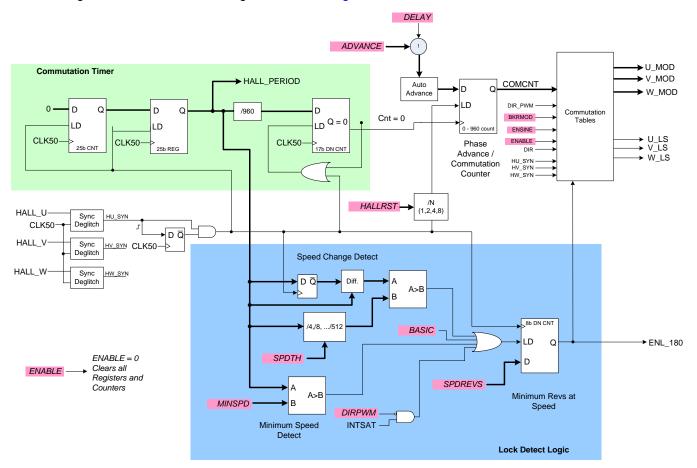


Figure 11. Commutation Logic

8.3.6 Commutation Parameters

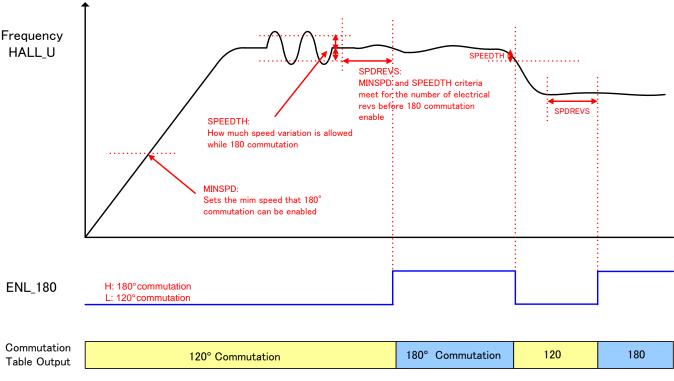
A number of commutation parameters are programmable through registers accessed through the serial interface, including:

- ADVANCE The phase of commutation is advanced (or delayed) relative to the Hall sensor transition by this 8-bit amount. Units are in commutation clocks, which is 1 / 960 of the HALL_U period. Note that phase advance is only applicable in single-Hall commutation modes. An automatic phase advance compensation mode can also be enabled by the AUTOADV bit (see Auto Gain and Advance Compensation for details).
- DELAY if set, commutation is delayed relative to Hall transitions; if cleared, commutation is advanced relative to Hall transitions.
- BASIC The BASIC bit, when set, prevents single-Hall or 180° commutation from being entered regardless of the above parameters, forces conventional 120° commutation, and disables ADVANCE functionality.
- ENSINE The ENSINE bit, when set, selects 180° sinusoidal commutation. The BASIC bit must also be 0.
- HALLRST HALLRST sets how many HALL_U cycles pass for each commutation counter reset. In other words, the commutation counter is reset every N HALL_U edges. Selections available are 1, 2, 4, and 8.
- MINSPD Sets the minimum Hall_U period that LOCK can be set. The 8-bit field represents 2.56 ms/count, with a max value of 652.8 ms.
- SPDREVS After the MINSPD and SPEEDTH criteria are met, SPDREVS adds a minimum number of Hall_U periods that must occur for LOCK to be set.
- SPEEDTH Sets how much speed variation is allowed across Hall_U periods while keeping LOCK set. This 3-bit field sets the percentage variation allowed by changing a programmable divider. Divisions of 1/4, 1/8, 1/16, 1/32, 1/64, 1/128, 1/256, and 1/512 are supported. These divisors correspond to 25%, 12.5%, 6.25%,

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3.13%, 1.56%, 0.78%, 0.39%, and 0.20% variation per revolution.

The diagram below shows how the lock parameters (MINSPD, SPEEDTH, and SPDREV) affect commutation mode.





8.3.7 Braking

Motor braking can be initiated by the BRKPOL register bit as well as the BRAKE pin. The BRKPOL register bit can also be used to program the polarity of the BRAKE pin, as it is combined with the pin with an exclusive-OR function as follows:

BRAKE pin	BRKPOL Register Bit	Resulting Function
0	0	Not brake
0	1	Brake
1	0	Brake
1	1	Not brake

When the motor is braking, all low-side drivers are held in an on state, causing all low-side FETs to turn on, and the integrator is reset to 0.

In addition, braking can be entered when the ENABLE pin is made inactive. BRKMOD controls the behavior of the outputs when ENABLE is inactive. If BRKMOD= 0, the outputs are 3-stated, resulting in the motor coasting; if BRKMOD = 1, all low-side FETs are turned on, causing the motor to brake.

	BRKMOD = 0 COAST	BRKMOD = 1 BRAKE					
RESET = 1	Coast	Brake					
BRAKE = active	Brake	Brake					
ENABLE = inactive	Coast	Brake					



Table 5. BRRINDD (continued)					
	BRKMOD = 0 COAST	BRKMOD = 1 BRAKE			
DIR	Coast	Brake			
Clock off	Brake	Brake			
Power down	Coast	Brake			

Table 5. BRKMOD (continued)

8.3.8 Output Pre-Drivers

The output drivers for each phase consist of N-channel and P-channel MOSFET devices arranged as a CMOS buffer. They are designed to directly drive the gate of external N-channel power MOSFETs.

The outputs can provide synchronous or asynchronous rectification. In asynchronous rectification, only the highside FET is turned on and off with the PWM signal; current is recirculated using external diodes, or the body diodes of the external FETs. In synchronous rectification, the low side FET is turned on when the high side is turned off.

Synchronous rectification is enabled or disabled using the SYNRECT control bit. When set to 1, synchronous rectification is used. In general, synchronous rectification results in better speed control and higher efficiency.

The high-side gate drive output UHSG is driven to VCP whenever the duty cycle output U_PD from the PWM generator is high, the enable signal U_HS from the commutation logic is active, and the current limit (V_{LIMITER}) is not active. If the high-side FET is on and a current limit event occurs, the high-side FET is immediately turned off until the next PWM cycle.

The low-side gate drive ULSG is driven to VM whenever the internal signal U_LS is high, or whenever synchronous rectification is active and UHSG is low.

Phases V and W operate in an identical fashion.

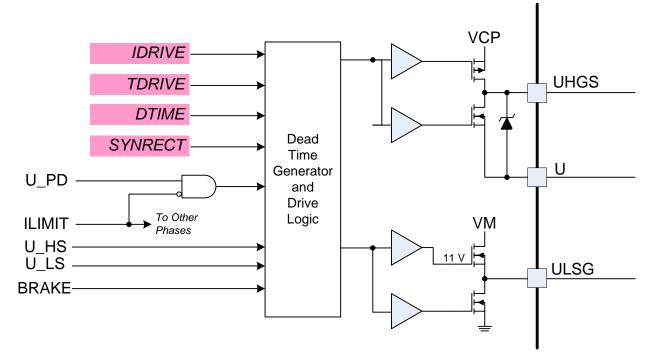


Figure 13.

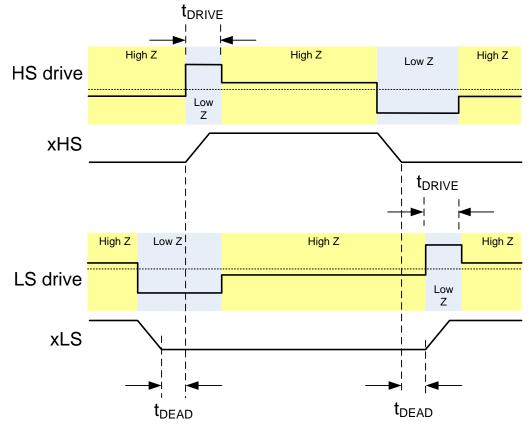


Figure 14.

The peak drive current of the pre-drivers is adjustable by setting the IDRIVE register bits. Peak drive currents may be set between 10 and 130 mA. Adjusting the peak current changes the output slew rate, which also depends on the FET input capacitance and gate charge.

When changing the state of the output, the peak current is applied for a short period of time (t_{DRIVE}), to charge the gate capacitance. This time is selected by setting the TDRIVE register bits. Times of 1, 5, 10, or 15 µs may be selected. After this time, a weak current source is used to keep the gate at the desired state. When selecting the gate drive strength for a given external FET, the selected current must be high enough to fully charge and discharge the gate during the time when driven at full current, or excessive power is dissipated in the FET.

During high-side turn-on, the low-side gate is held low with a low impedance. This prevents the gate-source capacitance of the low-side FET from inducing turn-on. Similarly, during low-side turn-on, the high-side gate is held off with a low impedance.

The pre-driver circuits include enforcement of a dead time in analog circuitry, which prevents the high-side and low-side FETs from conducting at the same time. Additional dead time can be added (in digital logic) by setting the DTIME register bits.

8.3.9 Current Limit

The current limit circuit activates if the voltage detected across the low-side sense resistor exceeds V_{LIMITER} . Note that the current limit circuit is ignored immediately after the PWM signal goes active for a short blanking time, to prevent false trips of the current limit circuit.

If current limit activates, the high-side FET is disabled until the beginning of the next PWM cycle. If synchronous rectification is enabled when the current limit activates, the low-side FET is activated while the high-side FET is disabled.



8.3.10 Charge Pump

Since the output stages use N-channel FETs, a gate drive voltage higher than the VM power supply is needed to fully enhance the high-side FETs. The DRV8308 device integrates a charge pump circuit that generates a voltage approximately 10 V more than the VM supply for this purpose.

The charge pump requires two external capacitors for operation. For details on these capacitors (value, connection, and so forth), refer to the Figure 2 and .

The charge pump is shutdown when in standby mode (ENABLE inactive).

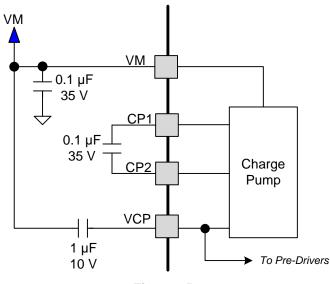


Figure 15.

8.3.11 5-V Linear Regulator

A 5-V linear regulator (VREG) is provided to power internal logic and external circuitry, such as the Hall effect sensors.

A capacitor must be connected from the VREG output to ground, even if the output is not used for external circuitry. The recommended capacitor value is a 0.1-µF, 10-V ceramic capacitor.

The VREG output is designed to provide up to 30-mA output current, but power dissipation and thermal conditions must be considered. As an example, with 24 V in and 20 mA out, power dissipated in the linear regulator is $19 \text{ V} \times 20 \text{ mA} = 380 \text{ mW}$.

The VREG regulator is shutdown in standby mode (when ENABLE is inactive).

8.3.12 Power Switch

A low-current switch is provided in the DRV8308 device that can be used to power the Hall sensors or other external circuitry through the VSW pin. When ENABLE is active the switch is turned on, connecting the VSW pin to VM. When ENABLE is inactive the switch is turned off (standby mode).

8.3.13 Protection Circuits

A number of protection circuits are included in the DRV8308 device. Faults are reported by asserting the FAULTn pin (an active-low, open-drain output signal), as well as setting the appropriate bit or bits in the FAULT register. Note that bits in the FAULT register remain set until either a 0 is written to them, RESET is asserted, or the device power is cycled.

8.3.13.1 VM Undervoltage Lockout (UVLO)

If the VM power supply drops, there may not be enough voltage to fully turn on the output FETs. Operation in this condition causes excessive heating in the output FETs. To protect against this, the DRV8308 device contains an undervoltage lockout circuit.

In the event that the VM supply voltage drops below the undervoltage lockout threshold (V_{UVLO}), the FAULTn pin is driven active and the motor driver is disabled. After VM returns to a voltage above the undervoltage lockout threshold, the FAULTn pin is high impedance and operation of the motor driver automatically resumes.

The UVLO bit in the FAULT register is set. This bit remains set until a 0 is written to the UVLO bit.

At power-up, the UVLO bit is set.

Note that register reads and writes are still possible during the UVLO condition, as long as VM stays above the VM reset threshold. If VM drops below the VM reset threshold, all registers are reset and register read or write is not functional.

8.3.13.2 VM Overvoltage (VMOV)

In some cases, if synchronous rectification is used, energy from the mechanical system can be forced back into the VM power supply. This can result in the VM power supply being boosted by the energy in the mechanical system, causing breakdown of the output FETs, or damaging the DRV8308 device. To protect against this, the DRV8308 device has overvoltage protection.

There are two overvoltage thresholds, selectable by the OVTH bit. An overvoltage event is recognized if the VM voltage exceeds the selected overvoltage threshold (VM_{OVLO}). Note that for the output FETs to be protected, they must be rated for a voltage greater than the selected overvoltage threshold.

In the event of an overvoltage, the FAULTn pin is pulled low. If synchronous rectification is enabled, the output stage is forced into asynchronous rectification. After VM returns to a voltage below the overvoltage threshold, the FAULTn pin is high impedance. If synchronous rectification was enabled prior to the overvoltage event, after a fixed 60-µs delay, synchronous rectification is re-enabled.

The VMOV bit in the FAULT register is set. This bit remains set until a 0 is written to the VMOV bit.

8.3.13.3 Motor Overcurrent (OCP)

Overcurrent protection (OCP) is provided on each FET in addition to the current limit circuit. The OCP circuit is designed to protect the output FETs from atypical conditions such as a short circuit between the motor outputs and each other, power, or ground.

The OCP circuit is independent from the current limit circuitry. OCP works by monitoring the voltage drop across the external FETs when they are enabled. If the voltage across a driven FET exceeds V_{FETOCP} for more than t_{FETOCP} an OCP event is recognized. V_{FETOCP} is configurable by register OCPTH and t_{FETOCP} is configurable by register OCPTH.

In addition to monitoring the voltage across the FETs, an OCP event is triggered if the voltage applied to the ISEN pin exceeds the V_{SENSEOCP} threshold voltage.

In the event of an OCP event, FAULTn is pulled low, and the motor driver is disabled.

After a fixed delay of 5 ms, the FAULTn pin is driven inactive and the motor driver is re-enabled.

The OCP bit in the FAULT register is set when an OCP event is recognized. This bit remains set until a 0 is written to the OCP bit.

8.3.13.4 Charge Pump Failure (CPFAIL)

If the voltage generated by the high-side charge pump is too low, the high-side output FETs are not fully turned on, and excessive heating results. To protect against this, the DRV8308 device has a circuit that monitors the charge pump voltage.

If the charge pump voltage drops below VCPFAIL, the FAULTn pin is pulled low and the motor driver is disabled. After the charge pump voltage returns to a voltage above the VCPFAIL threshold, the FAULTn pin is high impedance and operation of the motor driver automatically resumes.

The CPFAIL bit in the FAULT register is set when the charge pump voltage drops below VCPFAIL. This bit remains set until a 0 is written to the CPFAIL bit.

At power-up, the CPFAIL bit is set.

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8.3.13.5 Charge Pump Short (CPSC)

To protect against excessive power dissipation inside the DRV8308 device, a circuit monitors the charge pump and disables it in the event of a short circuit on the PCB.

If a short circuit is detected on the charge pump, the FAULTn pin is pulled low and the motor driver is disabled. After a fixed period of 5 s, the FAULTn pin is high impedance and operation of the motor driver automatically resumes. If the short circuit condition is still present, the cycle repeats.

The CPSC bit in the FAULT register is set when a short circuit is detected on the charge pump. This bit remains set until a 0 is written to the CPSC bit.

8.3.13.6 Rotor Lockup (RLOCK)

Circuitry in the DRV8308 device detects a locked or stalled rotor. This can occur in the event of a mechanical jam or excessive torque load that causes the motor to stop rotating while enabled. The rotor lock condition is set if there are no transitions detected on the FGOUT signal for a programmable period of time (set by the LRTIME register bits). RLOCK can also occur if the 3 Hall signals are an invalid state (all High or all Low), which can be caused by a bad wire connection.

If a locked rotor condition is recognized, the FAULTn pin is pulled low, the motor driver is disabled and the RLOCK bit in the FAULT register is set. The RLOCK bit remains set until a 0 is written to the RLOCK bit.

If the RETRY bit is set, the part re-enables itself after a fixed delay of 5 s.

If the RETRY bit is not set, the part disables the pre-drivers until RESET is asserted, or power has been removed and reapplied to the device.

8.3.13.7 Overtemperature (OTS)

To protect against any number of faults that could result in excessive power dissipation inside the device, the DRV8308 device includes overtemperature protection.

Overtemperature protection activates if the temperature of the die exceeds the OTS threshold temperature (T_{TSD}). If this occurs, the FAULTn pin is pulled low, the device is disabled and the OTS bit in the FAULT register is set. This OTS bit remains set until a 0 is written to the OTS bit.

If the RETRY bit is set after the temperature has fallen below the OTS threshold, the part re-enables itself after a fixed delay of 5 s.

If the RETRY bit is not set, the part disables the pre-drivers until RESET is asserted, or until power has been removed and re-applied to the device.

8.3.14 Serial Interface

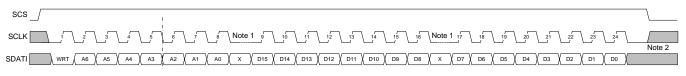
A simple SPI serial interface is used to write to the control registers in the DRV8308 device. Optionally, the interface can be configured to automatically load the registers from an external EEPROM device.

Data is shifted into a holding register when SCS is active high. When SCS is returned to inactive (low), the data received is latched into the addressed register.

8.3.15 Serial Data Format

The serial data consists of a 24-bit serial write, with a read or write bit, 7 address bits, and 16 data bits. The address bits identify one of the registers defined in Table 7.

To write to a register, data is shifted in after the address as shown in Figure 16:



A. Any amount of time may pass between bits, as long as SCS stays active high. This allows 8-bit writes to be used.

B. Any additional clock edges encountered after the 24th edge are ignored.

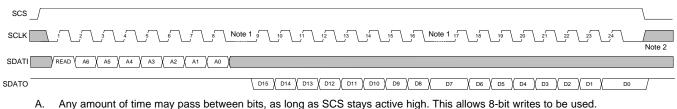
Figure 16. Timing Diagram



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Data may be read from the registers through the SDATO pin. During a read operation, only the address is used form the SDATI pin; the data bits following are ignored. Reading is enabled by setting the READ bit at the beginning of the access:



B. Any additional clock edges encountered after the 24th edge are ignored.

Figure 17.

8.3.16 Programming the OTP Configuration Memory

To permanently program data in to the internal OTP memory, data is first written into the internal registers described previously.

To write all of the register values into the OTP, follow this sequence:

ADDRESS	DATA	ACTION						
0x2Dh	0x1213h	write						
0x2Dh	0x1415h	write						
0x2Dh	0x1617h	write						
0x2Dh	0x1819h	write						
0x39h	0x0002h	write						
		wait 10 ms minimum						
0x2Dh	0EDDh	write						

Table 6.

The internal OTP memory can only be programmed once. After programming, the registers can still be overwritten by accesses through the SPI port, or by using an external EEPROM.



8.4 Device Functional Modes

8.4.1 Speed Control

The DRV8308 device is designed to support a wide range of motor speeds and constructions. Speeds of up to approximately 50000 RPM are supported with motor constructions of up to 16 poles, or corresponding lower speeds with more poles. This translates into a Hall sensor speed of up to 6.7 kHz. (The frequency of one Hall sensor can be calculated by RPM × (motor poles) / 120.)

Speed control of the motor is accomplished by varying the duty cycle of the PWM outputs. Three methods of speed control input are possible with the DRV8308 device:

- Clock frequency mode: uses a clock input that is frequency-locked to the FG frequency, for closed-loop speed control.
- Clock PWM mode: uses a clock input with duty cycle information to control the speed of the motor. This is open-loop.
- Internal register PWM mode: uses a programmed register value that represents duty cycle to control the speed of the motor. This is open-loop.

The speed mode is selected by the SPDMODE register.

8.4.1.1 Clock Frequency Mode

In clock frequency mode, the clock signal is deglitched by the 51.2-MHz clock. The deglitched input, along with the FG signal (derived from the FG amplifier, TACH input, or the Hall sensors), are input to a speed differentiator, where the CLKIN signal is compared to the actual speed of the motor (determined by the FG frequency). The speed differentiator outputs are UP and DOWN pulses.

The deglitcher and speed differentiator are shown in Figure 18:

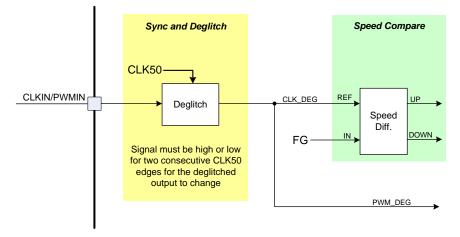


Figure 18. Clock Frequency Mode

The UP and DOWN outputs of the speed differentiator are integrated by accumulating the value set by the SPDGAIN register for each cycle of the integrator clock (CLK50 divided by the value of the INTCLK register) that an UP or DOWN signal is active. If UP is active, the amount is added to the current integrator output; if the DOWN input is active, the value is subtracted. If neither signal is active, the integrator output remains the same. Note that the integrator output is reset to 0 at any time the motor is disabled or in brake, and at reset. The integrator output does not roll over at maximum or minimum count.

At the moment that ENABLE is made active, the integrator and filters are reset to 0. If there are no transitions on the CLKIN pin, no UP pulses are generated, so the integrator remains at 0, and the motor is not driven.

Once the motor is running, if the signal on CLKIN stops, DOWN pulses are generated until the integrator reaches 0. This actively decelerates the motor (brake) until the motor stops.



Device Functional Modes (continued)

The output of the integrator is applied to a programmable digital filter. The filter has one pole and one zero. The pole location is programmable from approximately 100 to 1600 Hz, and is set via the FILK1 register; the zero location is programmable from 2 to 100 Hz and is set via the FILK2 register. The filter may be bypassed by setting the BYPFILT bit.

For a given pole and zero frequency, FILK1 and FILK2 are calculated as follows:

$$FILK2 = 2^{19} \frac{2\pi \frac{f_z}{f_s}}{1 + \pi \frac{f_z}{f_s}}, \qquad FILK1 = 2^{16} \frac{2\pi \frac{f_p}{f_s}}{1 + \pi \frac{f_p}{f_s}}$$

where

- f_z is the desired zero frequency
- f_p is the desired pole frequency
- f_s is the filter sample rate (195000 Hz)
- The result is rounded to the nearest integer

(1)

Following the filter is a programmable lead compensator, which also contains one pole and one zero. The compensator characteristics are programmable by the COMPK1 and COMPK2 registers. Center frequency is programmable between 20 and 100 Hz, with a phase lead between 0° and 80°. The compensator may be bypassed by setting the BYPCOMP bit.

For a given pole and zero frequency, COMPK1 and COMPK2 are calculated as follows:

COMPK2 =
$$2^{19} \frac{2\pi \frac{f_z}{f_s}}{1 + \pi \frac{f_z}{f_s}}$$
, COMPK1 = $2^{16} \frac{2\pi \frac{f_p}{f_s}}{1 + \pi \frac{f_p}{f_s}}$

where

- f_z is the desired zero frequency
- f_p is the desired pole frequency
- f_s is the filter sample rate (195000 Hz)
- The result is rounded to the nearest integer

(2)

To calculate the parameters from a center frequency and desired phase lead, a tabular estimation is used. Consult the factory for a spreadsheet to aid in this calculation.

The digital filter and compensator are reset to 0 whenever the motor is disabled.

The integrator, filter, and lead compensator result in a typical open-loop response as shown in Figure 19. Note that the locations of the poles and zeros are not restricted to what is shown.

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Device Functional Modes (continued)

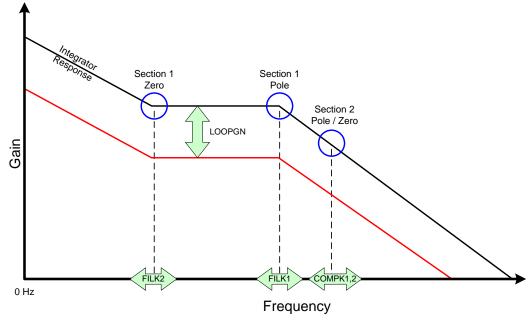


Figure 19. Open-Loop Response

The integrator and filters are shown in Figure 20:

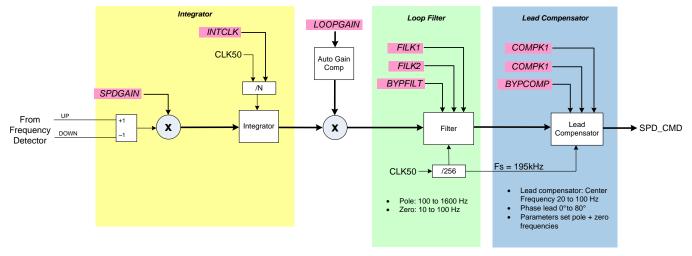


Figure 20. Integrator and Filters

The output of the filters is a speed command, SPD_CMD.

8.4.1.2 Clock PWM and Internal Register PWM Modes

In PWM input modes, the PWM input signal is timed using a 50 MHz clock to generate a 12-bit number that corresponds to the duty cycle of the incoming PWM signal. The input PWM frequency should be between 16 and 50 kHz, higher PWM frequencies work, but resolution is degraded. Note that the gate driver's output PWM frequency is independent of the speed control PWM input frequency; the output PWM frequency is selected by the PWMF register bits.

The measured input duty cycle is scaled by the contents of the MOD120 register. With a full-scale MOD120 register (4095 decimal), the output duty cycle is 2× the input duty cycle. To make the output duty cycle equal to the input, a value of 2048 decimal should be written to MOD120.



Device Functional Modes (continued)

An additional multiplication factor of 2 is introduced when the BYPCOMP bit is set; if BYPCOMP is set, the output duty cycle is 4× the input duty cycle (when MOD120 is 4095).

In register speed control mode, a 12-bit register SPEED is used to directly provide the speed command.

During sine commutation, the input duty cycle is multiplied by the modulation values for each phase (MOD_U, MOD_V, and MOD_W) to generate a 12-bit value that determines the output PWM duty cycle of each phase. Note that in 120° commutation, the MOD values are fixed at a duty cycle that is set by the MOD120 register.

The PWM frequency can be set to either 25, 50, 100, or 200 kHz, with register PWMF. Lower PWM frequencies are desirable to minimize switching losses; higher PWM frequencies provide better control resolution, especially at very high motor speeds.

The outputs of the PWM generators are the signals U_PD, V_PD, and W_PD. These contain the duty cycle information for each phase.

Modulation and PWM generation is shown in Figure 21:

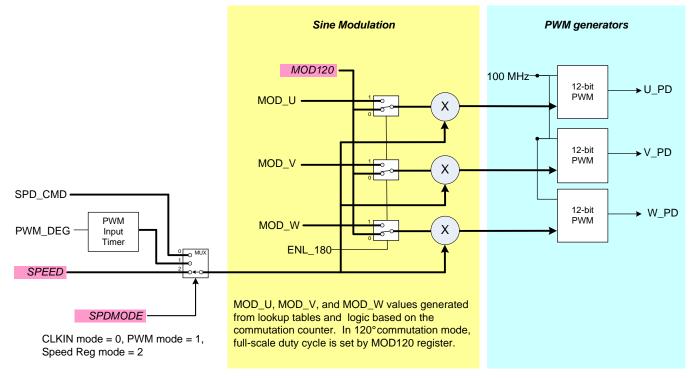


Figure 21. Modulation and PWM Generation

8.4.2 Auto Gain and Advance Compensation

The DRV8308 device provides modes to automatically scale the loop gain and the phase advance settings based on motor speed. This helps improve loop stability and motor performance in cases where the motor must operate over a wide speed range with a single set of parameters. For applications that run at only one speed, these functions should be left disabled.

Auto gain compensation is enabled by setting the AUTOGAIN bit. Auto gain will scale the LOOPGAIN of the system using the following equation (the DC gain that FLK2/FILK1 and COMK2/COMK1 are still in effect):

Computed Gain = LOOPGAIN / AG_SETPT × f_{CLKIN}

(3)

Automatic advance is enabled by setting the AUTOADV bit. The advance setting is scaled such that at zero speed, there is no phase advance. As speed increases, the phase advance is increased using the equation below:

Computed Advance = ADVANCE / AAA_SETPT × f_{Hall_U}

Device Functional Modes (continued)

Both the gain and advance values are latched when LOCK goes active (when the motor is at constant speed).

The auto gain and advance functions are shown in Figure 22:

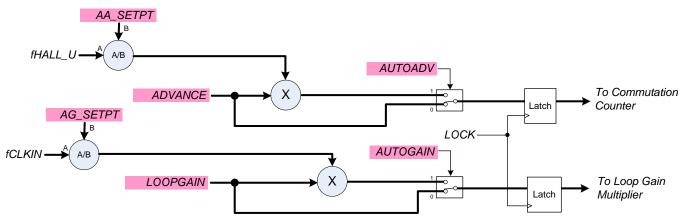
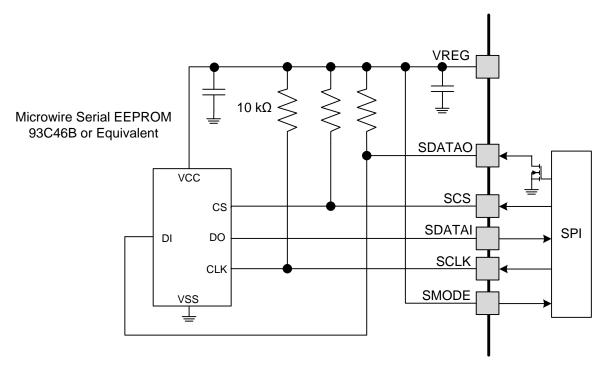


Figure 22. Auto Gain and Advance Functions

8.4.3 External EEPROM Mode

A serial EEPROM can be connected to the serial port to load the register contents. To activate external EEPROM mode, connect the SMODE pin to logic high. This causes the SPI interface to act as a master, and load data from an external EEPROM. The DRV8308 device latches data on the falling edge of SCLK.

The serial EEPROM should be a microwire-compatible, 16-bit-word device, such as the 93C46B. The VREG power supply can be used to power the EEPROM. Connections are as shown in Figure 23:





Data in the EEPROM should be arranged starting at address 0 exactly as shown in Table 6. EEPROM data bits 12 to 15 are unused.



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Device Functional Modes (continued)

To program the EEPROM device in-circuit while connected to the DRV8308 device, place the DRV8308 device into the reset state by driving RESET high. This 3-states the serial interface pins and allows them to be overdriven by external programming logic. Alternatively, the EEPROM may be programmed off-board before assembly. The DRV8308 device cannot program an EEPROM.

8.5 Register Map

8.5.1 Control Registers

The DRV8308 device uses internal registers to set operation parameters, including the characteristics of the speed control loop, commutation settings, gate drive current, and so forth. The registers are programmed through a serial SPI communications interface. In addition, the registers can be permanently programmed into non-volatile OTP memory, or loaded from an external serial EEPROM device.

This is the register map:

Address	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
0x00	AG_SETPT ENPOL DIRPOL BRKPOL SYNRE					SYNRECT	PW	MF	SPDMODE FGS			SEL	BRKMOD	RETRY			
0x01	RSVD							ADVANCE									
0x02	SPDREVS								MIN	SPD							
0x03	BASIC		SPEEDTH							MO	0120						
0x04	LRTIME HALLRST			LRST	DELAY	AUTOADV	AUTOGAIN	ENSINE	TDF	RIVE		DTIME			IDRIVE		
0x05	RSVD		INTCLK			SPDGAIN											
0x06	HALLPOL	RS	SVD	BYPFILT						FIL	FILK1						
0x07		RS	SVD						FILK2								
0x08		RSVD		BYPCOMP						CO	MK1						
0x09		AA_S	ETPT							CO	MK2						
0x0A	OCP	DEG	OC	PTH	OVTH	OVTH VREG_EN LOOPGAIN											
0x0B	RSVD					SPEED											
0x2A					RSVD					RLOCK	VMOV	CPFAIL	UVLO	OTS	CPOC	OCP	

Figure 24. Register Map

At power-up, when VM rises above the VM reset threshold, or whenever RESET is toggled, the register contents are loaded from the OTP memory or EEPROM (depending on SMODE). For details on external EEPROM connections, see External EEPROM Mode. If the OTP has not been programmed and the DRV8308 device is powered-up with SMODE low, the default register values are all 0, except for the FAULT register, which defaults to 0x18. FAULT bits can be cleared by writing 0.

At any time, the register contents may be written or overwritten through the SPI interface.

For detailed descriptions for each register, refer to the prior sections.

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Register Map (continued)

Table 7. Register Descriptions

ADDRESS	BIT	NAME		DESCRI	PTION		TYPE ⁽¹⁾			
			Autogain Setpoint							
	15:12	AG_SETPT	0000 = 3 Hz 0001 = 6 Hz 0010 = 12 Hz 0011 = 24 Hz	0100 = 48 Hz 0101 = 95 Hz 0110 = 191 Hz 0111 = 382 Hz	1000 = 763 Hz 1001 = 1.5 kHz 1010 = 3 kHz 1011 = 6 kHz	1100 = 12 kHz 1101 = 24 kHz 1110 = 49 kHz 1111 = 98 kHz	RW			
			ENABLE pin polarity	NABLE pin polarity						
	11	ENPOL	0 = Device is active w 1 = Device is active w				RW			
			DIR pin polarity							
	10	DIRPOL	0 = Normal direction v 1 = Normal direction v				RW			
			BRAKE pin polarity							
	9	BRKPOL	0 = Brake when BRAK 1 = Brake when BRAK				RW			
			Synchronous rectificat	ion						
	8	SYNRECT	0 = Disabled 1 = Enabled				RW			
0x00 7:6		The PWM frequency u	used on the external FET	S						
	PWMF	00 = 25 kHz 01 = 50 kHz 10 = 100 kHz 11 = 200 kHz				RW				
			Speed control mode							
	5:4	SPDMODE	00 = Clock frequency 01 = Clock PWM mod 10 = Internal register I 11 = Reserved	e			RW			
			FG select							
	3:2	FGSEL	00 = Use HALL_U to g 01 = Use XOR of all th 10 = Use FG amplifier 11 = Use TACH input	rree Hall sensors			RW			
			Motor brake mode							
	1	BRKMOD		BLE is inactive (outputs 3 BLE is inactive (all low-sic			RW			
			Retry mode							
	0	RETRY	0 = Latch off in case of 1 = Automatic retry in				RW			
0x01	15:8	RSVD	Reserved				-			
0.001	7:0	ADVANCE	° °	dvance versus Hall signa			RW			
0x02	15:8	SPDREVS		I SPEEDTH criteria are n ust occur for LOCK to be		inimum number of	RW			
	7:0	MINSPD	Sets the minimum Hal	I_U period that LOCK ca	n be set; each count is 2	.56 ms	RW			
	45	DAGIO	Basic operation				D 144			
	15	BASIC	0 = Normal device ope 1 = Disables ADVANC	eration E functionality and force	s 3-Hall 120° commutatio	on	RW			
0x03			Speed change toleran	ce for LOCK						
	14:12 SPEEDTH 000 = 1/512 rev (0.20%) 011 = 1/64 rev (1.56%) 110 = 1/8 rev (12.5%) 001 = 1/256 rev (0.39%) 100 = 1/32 rev (3.13%) 111 = 1/4 rev (25%) 010 = 1/128 rev (0.78%) 101 = 1/16 rev (6.25%)					,	RW			
	11:0	MOD120	Scales the input duty				RW			

(1) R = Read Only; RW = Read or Write. Fault registers can only be written 0.



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Register Map (continued)

Table 7	Register	Descriptions	(continued)
Table 7.	Register	Descriptions	(continueu)

ADDRESS	BIT	NAME		DESCR	IPTION	TYPE ⁽¹⁾				
			Locked rotor timeout							
	15:14	LRTIME	00 = RLOCK occurs after 1 s 01 = RLOCK occurs after 3 s 10 = RLOCK occurs after 5 s 11 = RLOCK occurs after 10 s							
			Sets the frequency to	reset the Hall commutat	ion counter					
	13:12	HALLRST	00 = Every Hall_U cycle 01 = Every 2 nd Hall_U cycle 10 = Every 4 th Hall_U cycle 11 = Every 8 th Hall_U cycle							
			Controls whether AD	VANCE leads or lags Hal	l signals					
	11	DELAY	0 = Commutate after 1 = Commutate befo			RW				
			Enables automatic a	dvance compensation						
	10	AUTOADV	0 = Disabled 1 = Enabled			RW				
			Enables automatic g	ain compensation						
0x04	9	AUTOGAIN	0 = Disabled 1 = Enabled			RW				
			Enables 180° sine w	ave current drive						
	8	ENSINE	0 = Disabled 1 = Enabled			RW				
			Predriver high-current drive time							
	7:6	TDRIVE	00 = 1 µs 01 = 5 µs 10 = 10 µs 11 = 15 µs	RW						
			Predriver dead time							
	5:3	DTIME	000 = 60 ns 001 = 120 ns 010 = 240 ns	011 = 500 ns 100 = 740 ns 101 = 1.0 µs	110 = 1.24 μs 111 = 1.5 μs	RW				
			Predriver output pea							
	2:0	IDRIVE	000 = 10 mA 001 = 20 mA 010 = 30 mA	011 = 50 mA 100 = 90 mA 101 = 100 mA	110 = 110 mA 111 = 130 mA	RW				
	15	RSVD	Reserved			_				
			Integrator clock frequ	iency						
0x05	14:12	INTCLK	000 = 50 MHz 001 = 25 MHz 010 = 12.5 MHz	011 = 6.3 MHz 100 = 3.1 MHz 101 = 1.6 MHz	110 = 0.8 MHz 111 = 0.4 MHz	RW				
	11:0	SPDGAIN	Speed compensator			RW				
			Hall polarity							
	15	HALLPOL	0 = Hall signal logic 1 = Hall signal logic	RW						
0x06	14:13	RSVD	Reserved			-				
0,00			Bypass the filter that FILK1 and FILK2 configure							
	12	BYPFILT	0 = Filter is enabled 1 = Filter is disabled (FILK1 and FILK2 are ignored)							
	11:0	FILK1	Filter coefficient that	sets the pole frequency		RW				
0x07	15:12	RSVD	Reserved							
	11:0	FILK2	Filter coefficient that	sets the zero frequency		RW				

Register Map (continued)

Table 7. Register Descriptions (continued)

ADDRESS	BIT	NAME	DESCRIPTION	TYPE ⁽¹⁾						
	15:13	RSVD	Reserved	_						
	-		Bypass the compensator (COMK1 and COMK2 are ignored)							
0x08	12	BYPCOMP	0 = Filter is enabled 1 = Filter is disabled (FILK1 and FILK2 are ignored)	RW						
	11:0	COMK1	Compensator coefficient that sets the pole frequency	RW						
			Autoadvance setpoint							
0x09	15:12	AA_SETPT	0000 = 3 Hz0100 = 48 Hz1000 = 763 Hz1100 = 12 kHz0001 = 6 Hz0101 = 95 Hz1001 = 1.5 kHz1101 = 24 kHz0010 = 12 Hz0110 = 191 Hz1010 = 3 kHz1110 = 49 kHz0011 = 24 Hz0111 = 382 Hz1011 = 6 kHz1111 = 98 kHz	RW						
	11:0	COMK2	Compensator coefficient that sets the zero frequency	RW						
			OCP deglitch time to ignore voltage spikes							
	15:14	OCPDEG	00 = 1.6 μs 01 = 2.2 μs 10 = 3.0 μs 11 = 5.0 μs	RW						
			Protection threshold for VFETOCP							
0x0A	13:12	OCPTH	00 = 250 mV 01 = 500 mV 10 = 750 mV 11 = 1000 mV							
			Protection threshold for VOVLO							
	11	OVTH	0 = 29 V = 34 V							
	10	VREG_EN	0 = VREG enabled only when ENABLE is active 1 = VREG always enabled							
	9:0	LOOPGAIN	ts the overall gain for the speed control loop							
0x0B	15:12	RSVD	eserved							
0X0B	11:0	SPEED	peed command for internal register PWM mode							
	15:7	RSVD	Reserved							
	6	RLOCK	Fault: rotor lockup 0 = Normal 1 = Fault detected	RW						
			Fault: VM overvoltage							
	5	VMOV	0 = Normal 1 = Fault detected	RW						
			Fault: charge pump undervoltage							
	4	CPFAIL	0 = Normal 1 = Fault detected (default on power up)	RW						
0x2A			Fault: VM undervoltage							
	3	UVLO	0 = Normal 1 = Fault detected (default on power up)	RW						
			Fault: overtemperature shutdown							
	2	OTS	0 = Normal 1 = Fault detected	RW						
			Fault: charge pump overcurrent	_						
	1	CPOC	0 = Normal 1 = Fault detected	RW						
			Fault: motor OCP							
	0	OCP	0 = Normal 1 = Fault detected	RW						



9 Applications and Implementation

9.1 Application Information

9.1.1 Internal Speed Control Loop Constraints

The DRV8308 device is a versatile speed controller and driver for small, 3-phase brushless motors. However, there are some limitations to its application.

The built-in speed control loop is designed to work optimally with motor electrical speeds from about 50 Hz up to 6.7 kHz. For an 8-pole motor, this translates into about 500 RPM up to more than 100000 RPM. For motors with higher pole counts, these speeds scale down; for lower pole counts, they scale up.

Operation is possible at slower or faster speeds, but speed control becomes less effective, especially if using the Hall sensors for speed feedback (as opposed to the FG input).

Typically, the speed loop is optimized (by setting the filter coefficients and gains) at one desired motor speed. Operation is possible with one set of parameters over a limited speed range (for example, 1000 RPM to 2000 RPM), However, operation over a very wide speed range requires different parameters. The use of the auto gain and auto advance features can extend the dynamic range up to 4x.

When using the SPI interface to program the registers, the parameters can be updated at any time, even while the motor is running. In this manner, a wider range of speeds can be accommodated by the speed loop.

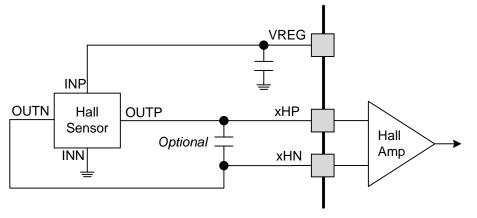
When not using the internal speed loop (when controlling the motor using PWM input or register speed control), the limits imposed by the speed loop do not apply. An external speed control implementation (using a microcontroller, FPGA, or other logic) can essentially control the motor current directly.

However, if using sine commutation, there are limits to the minimum and maximum speed, which are dictated by the timers that are used to generate the commutation sequence. The commutation timer is a 25-bit timer clocked at 50 MHz; therefore, the longest time it can capture is 655 ms. This limits the slowest speed to about 1.5 Hz (or 23 RPM for an 8-pole motor). At the other extreme, there are 960 steps in each sine commutation cycle. To ensure that there is enough time for the steps, the maximum speed is that which generates 960 counts at 50 MHz, or 52 kHz. This corresponds to a maximum speed of 800000 RPM for an 8-pole motor.

When not using the internal speed loop and using 120° commutation (using all three Hall sensors), there are no speed limitations. Commutation is performed with combinational logic.

9.1.2 Hall Sensor Configurations and Connections

The Hall sensor inputs on the DRV8308 device are capable of interfacing with a variety of Hall sensors. Typically, a Hall element is used, which outputs a differential signal on the order of 100 mV. To use this type of sensor, the VREG5 regulator can be used to power the Hall sensor. Connections are as shown in Figure 25:

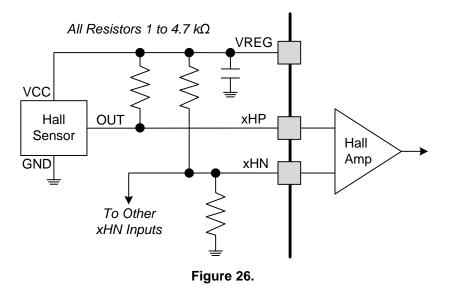




Since the amplitude of the Hall sensor output signal is very low, often capacitors are placed across the Hall inputs to help reject noise coupled from the motor PWM. Typically capacitors from 1 to 10 nF are used.

Application Information (continued)

Some motors use digital Hall sensors with open-drain outputs. These sensors can also be used with the DRV8308 device, with the addition of a few resistors:



The negative (xHN) inputs are biased to 2.5 V by a pair of resistors between VREG and ground. For opencollector Hall sensors, an additional pullup resistor to VREG is needed on the positive (xHP) input. Again, the VREG output can usually be used to supply power to the Hall sensors.

9.1.3 FG Amplifier Configurations and Connections

To improve speed control by providing a higher bandwidth speed feedback, often a magnetic pickup coil, commonly referred to as an FG generator, is used. This is typically implemented as a serpentine PCB trace on the motor PCB. This generates a low-level sine wave signal whose amplitude and frequency is proportional to the speed of the motor.

Since the FG trace is in close proximity to the motor coils, it is very susceptible to noise coupling from the PWM of the motor. Noise coupling into the FG circuit causes poor speed regulation, especially at low motor speeds. Startup is a particularly difficult situation, as the motor current is at a maximum, and the FG signal amplitude is low (in fact, 0 at the moment of startup). If noise couples into FG during startup, the speed loop interprets the noise as fast motor rotation, and lowers the PWM duty cycle. The result is slow startup of the motor. If this problem is suspected, looking at the FGOUT signal with an oscilloscope during startup should reveal it.

To address this, in addition to the resistors that set the gain of the FG amplifier (R1 and R2 in Figure 27), usually passive filter components are needed on the FG amplifier circuit.



Application Information (continued)

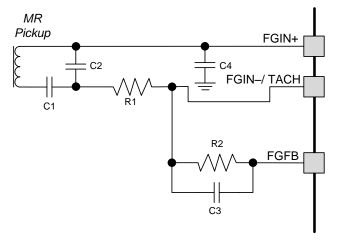


Figure 27.

Ideally, the user desires a large amount of rejection of the PWM frequency. However, the user needs to pass the frequency that corresponds to their fastest motor speed. As an example, a motor may put out 36 FG pulses per revolution. At 5000 RPM, this is a 3-kHz signal. If you operate the PWM at 25 kHz, you can set a single pole at 3 kHz and have significant rejection of the PWM frequency, and the higher harmonics of the PWM (which are typically more easily coupled) are rejected even more.

Because the amplitude of the FG signal also increases with higher motor speed, it is possible to set this pole at a much lower frequency than the maximum speed dictates. The optimal values need to be determined by testing on the actual motor.

This pole is set by C3 in Figure 27.

In addition to rejection of high frequency, the FG winding should be AC-coupled to the amplifier to prevent any issues with DC offsets. This capacitor (C1) must be large enough to allow the motor to start-up reliably, since the FG frequency and amplitude are very low at startup. Typically capacitors on the order of 100 nF to 1 μ F are used here. The voltage is low, so a 6.3-V ceramic capacitor can be used.

Occasionally an additional small capacitor is used across the FG trace. This capacitor (C2 above) may not be needed, but it can help reject very high-frequency harmonics of the PWM (glitches). Capacitors between 330 and 2200 pF are typically used.

9.1.4 **RESET and ENABLE Considerations**

Since the ENABLE function doubles as a sleep (low-power shutdown) function, there are some important considerations when asserting and deasserting ENABLE and RESET.

While the motor driver is enabled, the deassertion of ENABLE initiates a stop-and-power-down sequence. This sequence starts by disabling the motor (either braking or coasting depending on the BRKMOD bit), and waiting for rotation to stop. After rotation is stopped for 1 s (as determined by the absence of transitions on FGOUT), the internal circuitry is powered-down, the V5 regulator and power switch are disabled, and internal clocks are stopped.

In this low-power sleep state, the serial interface may still be used to read or write registers. All other logic is disabled.

After this stop-and-power-down sequence has been initiated (by deasserting the ENABLE pin for at least 1.2 μ s, or by changing the state of the ENPOL bit), the sequence continues to completion, regardless of the state of ENABLE. If ENABLE is immediately returned to the active state, the motor slows and stops for 1 s, at which point it starts again.

If RESET is asserted during power-down (at any time after the deassertion of ENABLE is recognized), it is acted upon when ENABLE is again asserted, and the part powers-up.

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Application Information (continued)

If RESET is asserted when ENABLE is active, the motor is stopped similar to the sequence when ENABLE is deasserted. After it is stopped for 1 s, all internal registers are reloaded with the value contained in OTP memory, faults are cleared, and internal states (that is, the speed loop datapath) are initialized. The motor remains disabled until RESET is deasserted.

RESET and ENABLE may be connected together (if the ENPOL bit in OTP memory is programmed so that ENABLE is active low). When both signals are low, the motor is enabled; when both signals are high, the motor is disabled. As soon as the signals are returned to high, all registers are reloaded from OTP memory, faults are cleared, and the motor starts.



10 Power Supply Recommendations

The DRV8308 device is designed to operate from an input voltage supply range between 8.5 and 32 V. This supply should be well regulated. TI recommends to use a 47-µF bulk capacitor to minimize transients on the supply.



11 Layout

11.1 Layout Guidelines

For VM, place 0.1- μ F bypass capacitor close to the device. Care should be taken to minimize the loop formed by the bypass capacitor connection from VM to GND.

12 Device and Documentation Support

12.1 Trademarks

All trademarks are the property of their respective owners.

12.2 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



19-Feb-2014

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
DRV8308RHAR	ACTIVE	VQFN	RHA	40	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	8308A0P	Samples
DRV8308RHAT	ACTIVE	VQFN	RHA	40	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85		Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

19-Feb-2014

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are	nominal												
Device		Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8308RH	HAR	VQFN	RHA	40	2500	330.0	16.4	6.3	6.3	1.5	12.0	16.0	Q2
DRV8308RI	TAT	VQFN	RHA	40	250	180.0	16.4	6.3	6.3	1.5	12.0	16.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

22-Feb-2014



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8308RHAR	VQFN	RHA	40	2500	367.0	367.0	38.0
DRV8308RHAT	VQFN	RHA	40	250	210.0	185.0	35.0

MECHANICAL DATA



All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. Α.

- Β. This drawing is subject to change without notice.
- QFN (Quad Flatpack No-Lead) Package configuration. C.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. D.
- See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions. Ε.
- F. Package complies to JEDEC MO-220 variation VJJD-2.



RHA (S-PVQFN-N40)

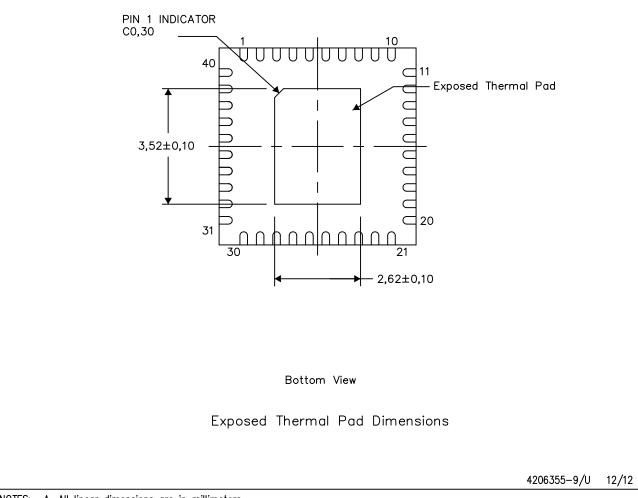
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

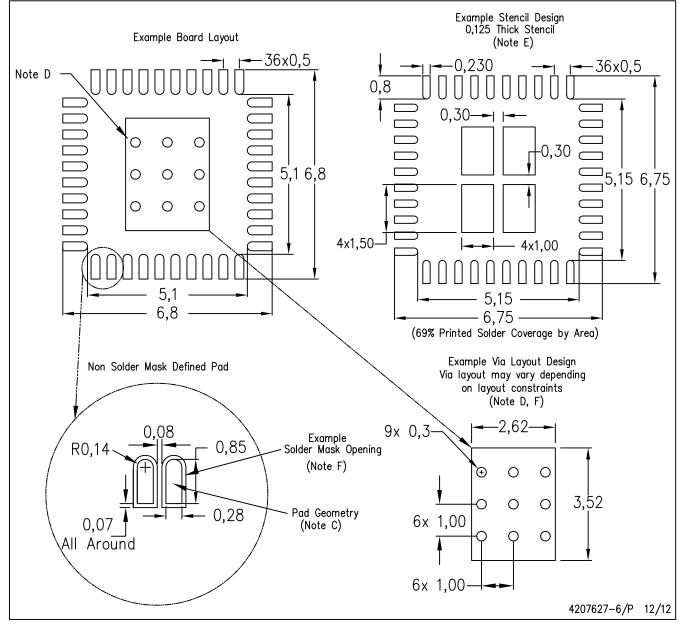


NOTES: A. All linear dimensions are in millimeters





PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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